# **Silicon Carbide Schottky Diode**

1200 V, 8 A

## **FFSD08120A**

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 80 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

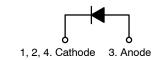
#### **Applications**

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

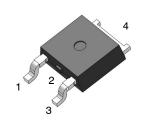


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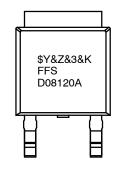


**Schottky Diode** 



DPAK3 CASE 369AS

#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code &K = Lot Code

FFSD08120A = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

#### FFSD08120A

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C unless otherwise noted)

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage	1200	V	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	80	mJ	
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 168°C		8	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> <	22.5	Α	
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	530	Α
		T <sub>C</sub> = 150°C, 10 μs	480	Α
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	77	Α
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	45	Α
P <sub>TOT</sub>	Power Dissipation	T <sub>C</sub> = 25°C	263	W
		T <sub>C</sub> = 150°C	44	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.57	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 8 A, T <sub>C</sub> = 25°C	-	1.45	1.75	V
		I <sub>F</sub> = 8 A, T <sub>C</sub> = 125°C	-	1.7	2.0	
		I <sub>F</sub> = 8 A, T <sub>C</sub> = 175°C	-	2.0	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25°C	-	-	200	μΑ
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 125°C	-	-	300	
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 175°C	-	-	400	
Q <sub>C</sub>	Total Capacitive Charge	V = 800 V	-	55	=	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	538	=	pF
		V <sub>R</sub> = 400 V, f = 100 kHz	-	50	=	
		V <sub>R</sub> = 800 V, f = 100 kHz	-	40	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **ORDERING INFORMATION**

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSD08120A	FFSD08120A	DPAK3	Tape & Reel <sup>†</sup>	13″	12 mm	2500 Units

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>1.</sup>  $E_{AS}$  of 80 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 18$  A, V = 50 V.

#### FFSD08120A

#### **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

10<sup>1</sup>

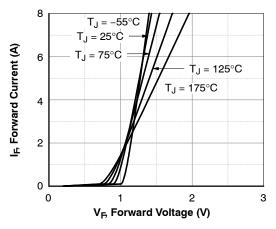
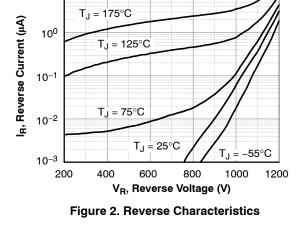


Figure 1. Forward Characteristics



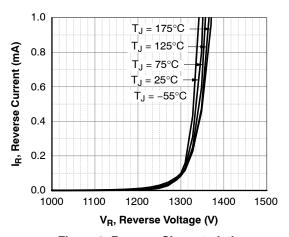


Figure 3. Reverse Characteristics

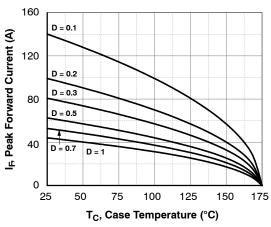


Figure 4. Current Derating

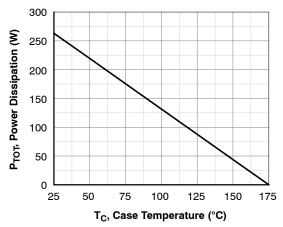


Figure 5. Power Derating

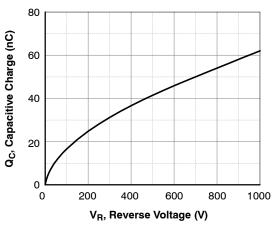


Figure 6. Capacitive Charge vs. Reverse Voltage

#### FFSD08120A

### TYPICAL CHARACTERISTICS (Continued)

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

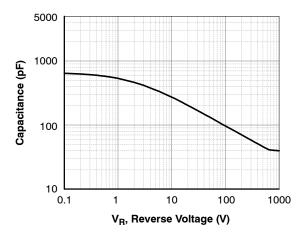


Figure 7. Capacitance vs. Reverse Voltage

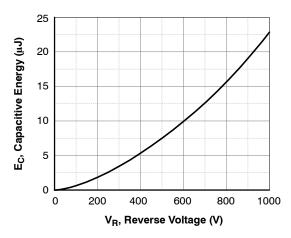


Figure 8. Capacitance Stored Energy

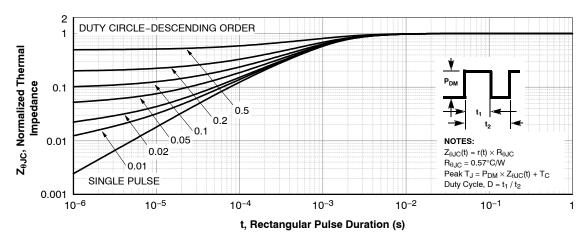
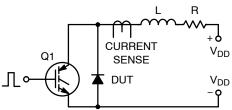


Figure 9. Junction-to-Case Transient Thermal Response Curve

#### **TEST CIRCUIT AND WAVEFORMS**

$$\begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \ \Omega \\ V_{DD} &= 50 \ V \\ EAVL &= 1/2 LI2 \left[ V_{R(AVL)} \ / \ (V_{R(AVL)} - V_{DD}) \right] \\ Q1 &= IGBT \ (BV_{CES} > DUT \ V_{R(AVL)}) \end{split}$$



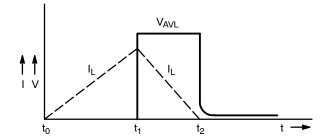
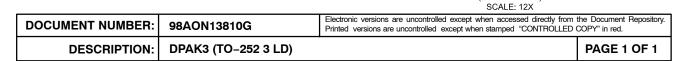


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

#### DPAK3 (TO-252 3 LD) CASE 369AS **ISSUE O DATE 30 SEP 2016** 6.73 6.35 5,46 5.55 MIN-6.50 MIN 6.40 Ċ 0.25 MAX PLASTIC BODY STUB MIN DIODE PRODUCTS VERSION (0.59)-1.25 MIN 0.89 ⊕ 0.25 M AM C 2.29 2.28 4.56 4.57 LAND PATTERN RECOMMENDATION NON-DIODE PRODUCTS VERSION В 2.39 SEE 2.18 4.32 MIN **NOTE D** 0.58 0.45 5.21 MIN 10.41 9.40 SEE DETAIL A 2 3 NON-DIODE PRODUCTS VERSION DIODE PRODUCTS VERSION ○ 0.10 B 0,51 **GAGE PLANE** NOTES: UNLESS OTHERWISE SPECIFIED 0.61 0.45 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, (1.54)ISSUE C, VARIATION AA. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONING AND TOLERANCING PER 10° ASME Y14.5M-2009. D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED 1 78 CORNERS OR EDGE PROTRUSION.



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E TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS

G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

F) DIMENSIONS ARE EXCLUSSIVE OF BURSS,

MOLD FLASH AND TIE BAR EXTRUSIONS.

0.127 MAX

**DETAIL A** (ROTATED -90°)

**SEATING PLANE** 

1,40

(2.90)

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